

# PSZ06080HM

800V 6A 900mΩ Si Super junction MOSFET with Zener Diode

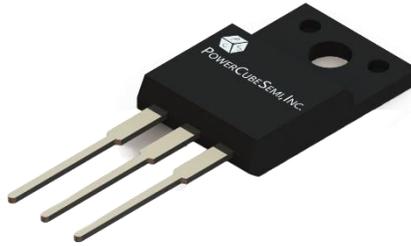
## Features

### Si Super junction MOSFET

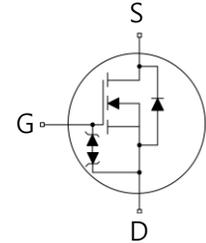
- Rated to 800V at 6Amps @ $T_J = 25^{\circ}\text{C}$
- Max  $R_{DS(on)} = 900\text{ m}\Omega$
- Typ  $R_{DS(on)} = 780\text{ m}\Omega$
- Gate Charge(Typ.  $Q_g = 13\text{ nC}$ )
- Low Power loss by High-Speed switching and low On-Resistance
- 100% Avalanche Tested

## Application

- PFC Power Supply Stages
- Switching Applications
- Adapter



PKG type : TO-220F



## Description

PSZ06080HM is Power MOSFET using PowerCubeSemi's advanced Super Junction technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of Low EMI to designers as well as low switching loss.

## Absolute Maximum Ratings

Symbol	Parameter	Test Condition	Value	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	800	V
$I_D$	Drain Current	$T_C=25^{\circ}\text{C}$	6	A
$I_{DM}$	Pulsed Drain Current	Pulse width limited by junction temperature	18	A
$V_{GS}$	Gate-Source Voltage		$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy		200	mJ
$P_d$	Power Dissipation	$T_C=25^{\circ}\text{C}$	62.5	W
$T_J$	Operating Junction Temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature		-55 to 150	$^{\circ}\text{C}$



## Package Marking and Ordering Information

Device Marking	Device	Package	Packing Method	Tape width	Quantity
PSZ06080HM	PSZ06080	TO-220F	Tube	-	50 unit

## Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical			Unit
			Min	Typ.	Max.	
$BV_{DSS}$	Drain-source breakdown voltage	$V_{GS} = 0V, I_D = 250\mu A, T_J = 25^\circ C$	800	-	-	V
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 800V, V_{GS} = 0V$	-	-	1	$\mu A$
$I_{GSS}$	Gate-source leakage current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	10	$\mu A$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	3.5	4.5	V
$R_{DS(ON)}$	Static drain-source on state resistance	$V_{GS} = 10V, I_D = 3.8A$ Pulse width = 200 $\mu s$	-	780	900	m $\Omega$
$t_{d(on)}$	Turn-on Delay time	$V_{DD} = 400V, I_D = 6A,$ $V_{GS} = 10V, R_G = 25\Omega$	-	18	-	ns
$T_r$	Turn-on Rise time		-	29	-	
$t_{d(off)}$	Turn-off Delay time		-	84	-	
$T_f$	Turn-off Fall time		-	19	-	



## Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
$R_{\theta JC}$	Thermal resistance, Junction to case		4.4	-	$^{\circ}\text{C}/\text{W}$
$R_g$	Gate resistance	$V_{GS} = 0\text{V}$ , $f = 1.0\text{MHz}$	29	-	$\Omega$
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 400\text{kHz}$	506	-	pF
$C_{oss}$	Output capacitance		21	-	
$C_{rss}$	Reverse transfer capacitance		0.8	-	
$Q_{g(\text{tot})}$	Total gate charge at 10V	$V_{DS} = 640\text{V}$ , $I_D = 6\text{A}$ $V_{GS(\text{on})} = 10\text{V}$	13	-	nC
$Q_{gs}$	Gate to source gate charge		4.3	-	
$Q_{gd}$	Gate to drain "Miller" charge		5.3	-	

## Electrical Characteristics of Si Diode

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
$I_S$	Maximum continuous drain to source diode forward current		-	6	A
$I_{SM}$	Maximum pulsed drain to source diode forward current		-	18	A
$V_{SD}$	Drain to source diode forward voltage	$I_{SD} = 6\text{A}$ , $V_{GS} = 0\text{V}$	-	1.4	V
$T_{rr}$	Reverse recovery time	$I_{SD} = 6\text{A}$ , $V_{DD} = 100\text{V}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$	375	-	ns
$Q_{rr}$	Reverse recovery charge		2.7	-	$\mu\text{C}$
$I_{rrm}$	Reverse recovery current		14	-	A

# Typical Characteristics

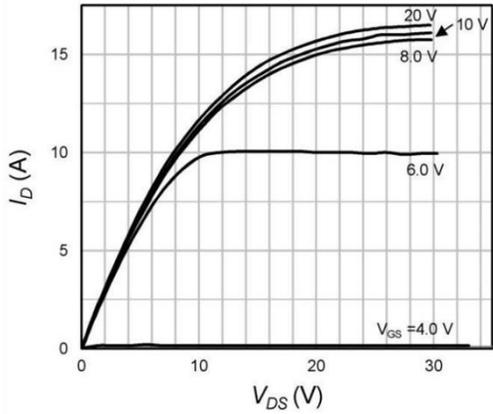


Figure 1. Output Characteristics

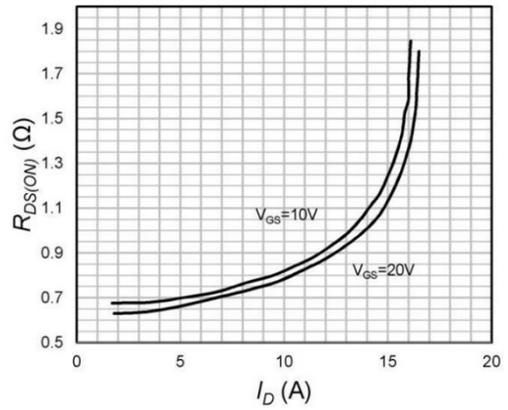


Figure 2. Drain-Source On-State Resistance vs. Drain Current

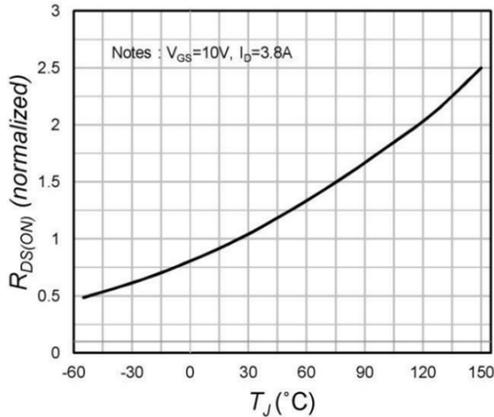


Figure 3. Drain-Source On-State Resistance (Normalized)

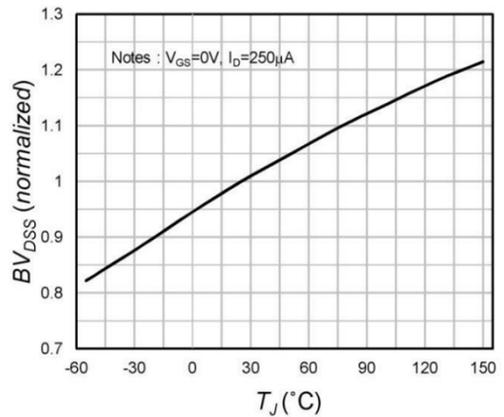


Figure 4. Drain-Source Breakdown Voltage (Normalized)

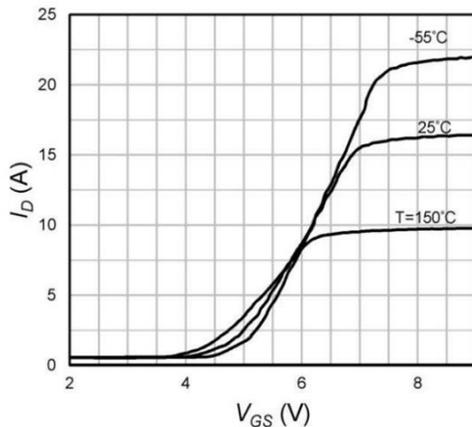


Figure 5. Transfer Characteristics

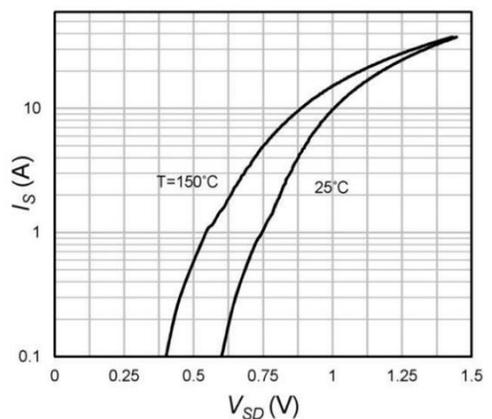


Figure 6. Forward Characteristics Of Reverse Diode

# Typical Characteristics

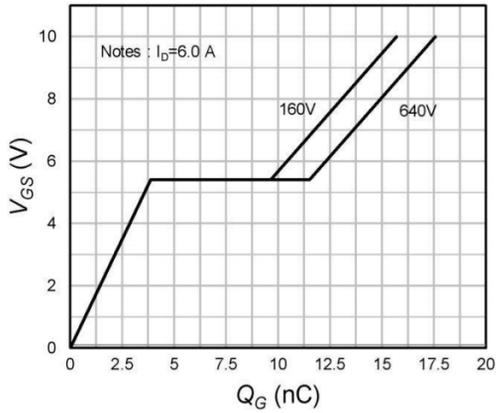


Figure 7. Gate Charge

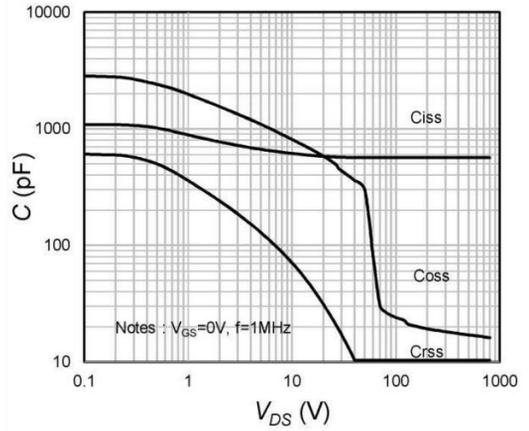


Figure 8. Capacitance Characteristics

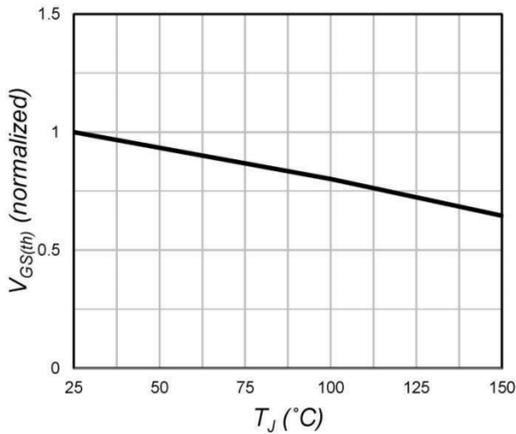


Figure 9.  $V_{GS(th)}$  variation vs. Temperature (Normalized)

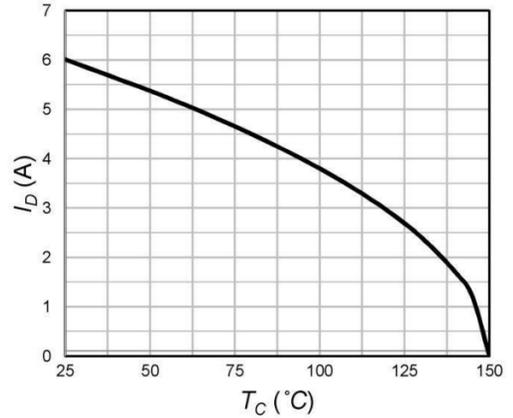


Figure 10. Maximum Drain Current vs. Case Temperature

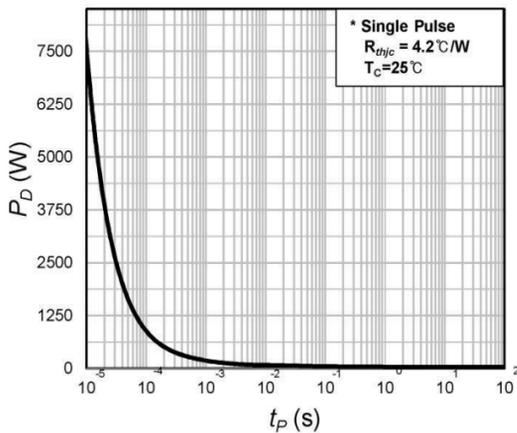


Figure 11. Power Dissipation

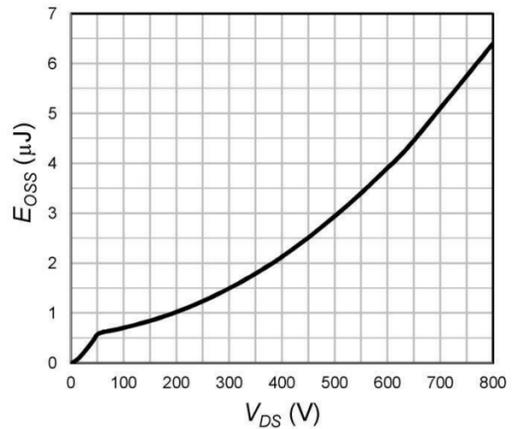


Figure 12. Output Capacitance stored energy

# Typical Characteristics

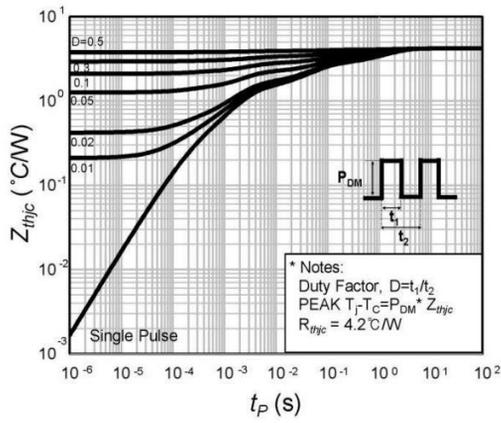


Figure 13. Transient thermal impedance

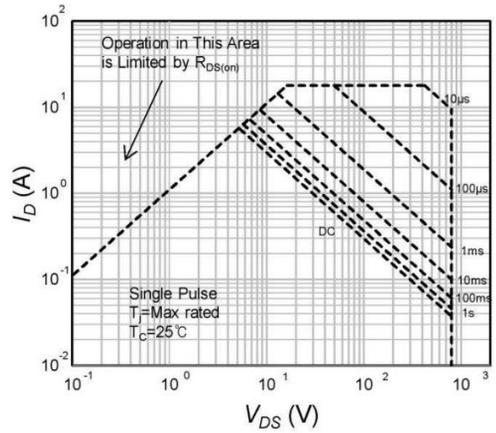
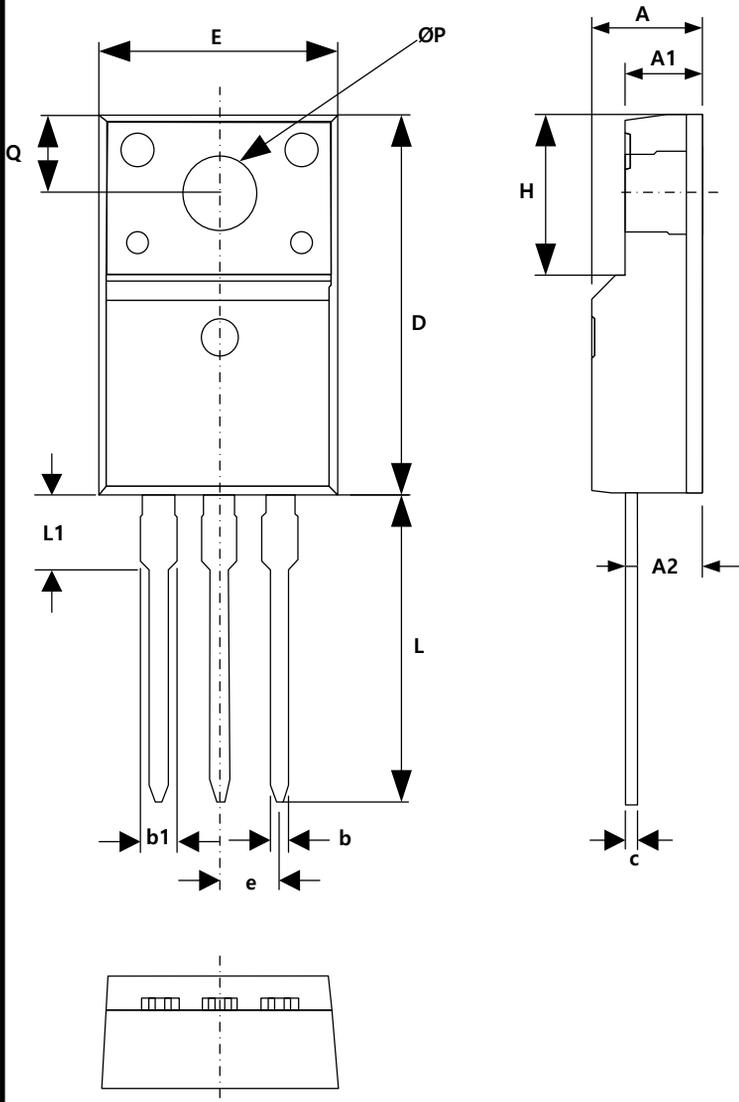


Figure 14. Safer operating area



**Package Outline**



[Unit : mm]

SYMBOL	DIMENSIONS		NOTES
	MIN	MAX	
A	4.50	4.90	
A1	2.34	2.74	
A2	2.56	2.96	
b	0.70	0.90	
b1	1.27	1.47	
c	0.45	0.60	
D	15.67	16.07	
E	9.96	10.36	
e	2.54 BSC		
H	6.48	6.88	
L	12.68	13.28	
L1	3.03	3.43	
$\phi P$	3.08	3.28	
Q	3.20	3.40	